

**GenX3™ 1200V
IGBTs**
**IXGK82N120A3
IXGX82N120A3**

$$V_{CES} = 1200V$$

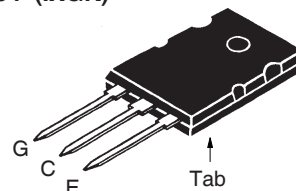
$$I_{C110} = 82A$$

$$V_{CE(sat)} \leq 2.05V$$

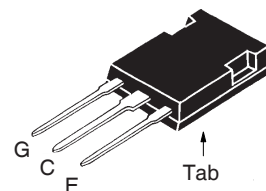
 Ultra-Low-V_{sat} PT IGBTs for
up to 3kHz Switching


Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ C$ to $150^\circ C$	1200	V
V_{CGR}	$T_J = 25^\circ C$ to $150^\circ C$, $R_{GE} = 1M\Omega$	1200	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ C$ (Chip Capability)	260	A
I_{C110}	$T_C = 110^\circ C$	82	A
I_{LRMS}	$T_C = 25^\circ C$ (Lead RMS Limit)	120	A
I_{CM}	$T_C = 25^\circ C$, 1ms	580	A
SSOA (RBSOA)	$V_{GE} = 15V$, $T_{VJ} = 125^\circ C$, $R_G = 2\Omega$ Clamped Inductive Load	$I_{CM} = 164$ @ $0.8 \cdot V_{CES}$	A
P_C	$T_C = 25^\circ C$	1250	W
T_J		-55 ... +150	$^\circ C$
T_{JM}		150	$^\circ C$
T_{stg}		-55 ... +150	$^\circ C$
T_L	Maximum Lead Temperature for Soldering	300	$^\circ C$
T_{SOLD}	1.6 mm (0.062 in.) from Case for 10	260	$^\circ C$
M_d	Mounting Torque (IXGK)	1.13/10	Nm/lb.in.
F_C	Mounting Force (IXGX)	20..120/4.5..27	N/lb.
Weight	TO-264	10	g
	PLUS247	6	g

TO-264 (IXGK)



PLUS247™ (IXGX)



G = Gate E = Emitter
C = Collector Tab = Collector

Features

- Optimized for Low Conduction Losses
- International Standard Packages

Advantages

- High Power Density
- Low Gate Drive Requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts
- Inrush Current Protection Circuits

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu A$, $V_{CE} = 0V$	1200		V
$V_{GE(th)}$	$I_C = 1mA$, $V_{CE} = V_{GE}$	3.0		5.0 V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$ Note 1, $T_J = 125^\circ C$			50 μA 2.5 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = I_{C110}$, $V_{GE} = 15V$, Note 2 $T_J = 125^\circ C$		1.83 1.95	2.05 V

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 60\text{A}$, $V_{CE} = 10\text{V}$, Note 2	40	66	S
C_{ies}	$V_{CE} = 25\text{V}$, $V_{GE} = 0\text{V}$, $f = 1\text{MHz}$		7700	pF
C_{oes}			520	pF
C_{res}			190	pF
$Q_{g(on)}$	$I_C = I_{C110}$, $V_{GE} = 15\text{V}$, $V_{CE} = 0.5 \cdot V_{CES}$		340	nC
Q_{ge}			54	nC
Q_{gc}			146	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 80\text{A}$, $V_{GE} = 15\text{V}$		34	ns
t_{ri}			75	ns
E_{on}			5.5	mJ
$t_{d(off)}$	Note 3		265	ns
t_{fi}			780	1300 ns
E_{off}			12.5	20.0 mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = 80\text{A}$, $V_{GE} = 15\text{V}$		32	ns
t_{ri}			77	ns
E_{on}			6.7	mJ
$t_{d(off)}$	Note 3		340	ns
t_{fi}			1250	ns
E_{off}			22.5	mJ
R_{thJC}			0.10	$^\circ\text{C/W}$
R_{thCK}			0.15	$^\circ\text{C/W}$

Notes:

1. Part must be heatsunk for high-temp I_{CES} measurement.
2. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
3. Switching times & energy losses may increase for higher $V_{CE}(\text{Clamp})$, T_J or R_G .

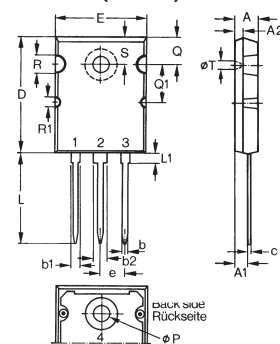
PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

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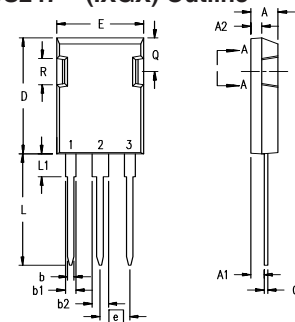
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

TO-264 AA (IXGK) Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.82	5.13	.190	.202
A1	2.54	2.89	.100	.114
A2	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b1	2.39	2.69	.094	.106
b2	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC .215 BSC			
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

PLUS247™ (IXGX) Outline



Terminals: 1 - Gate
2 - Drain (Collector)
3 - Source (Emitter)

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.83	5.21	.190	.205
A ₁	2.29	2.54	.090	.100
A ₂	1.91	2.16	.075	.085
b	1.14	1.40	.045	.055
b ₁	1.91	2.13	.075	.084
b ₂	2.92	3.12	.115	.123
C	0.61	0.80	.024	.031
D	20.80	21.34	.819	.840
E	15.75	16.13	.620	.635
e	5.45 BSC .215 BSC			
L	19.81	20.32	.780	.800
L1	3.81	4.32	.150	.170
Q	5.59	6.20	.220	0.244
R	4.32	4.83	.170	.190

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

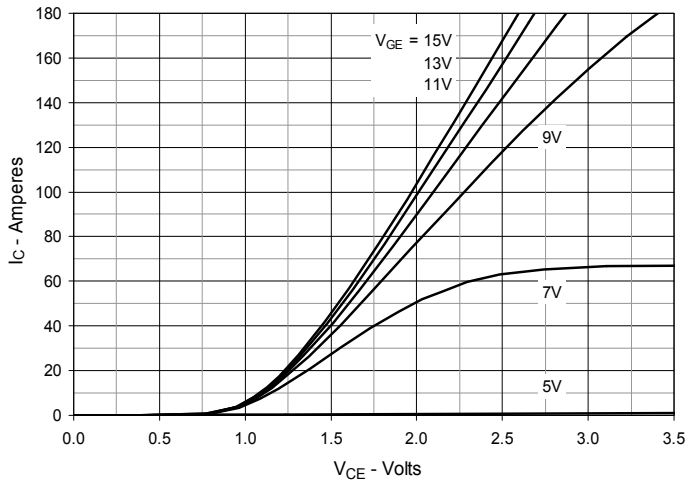


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

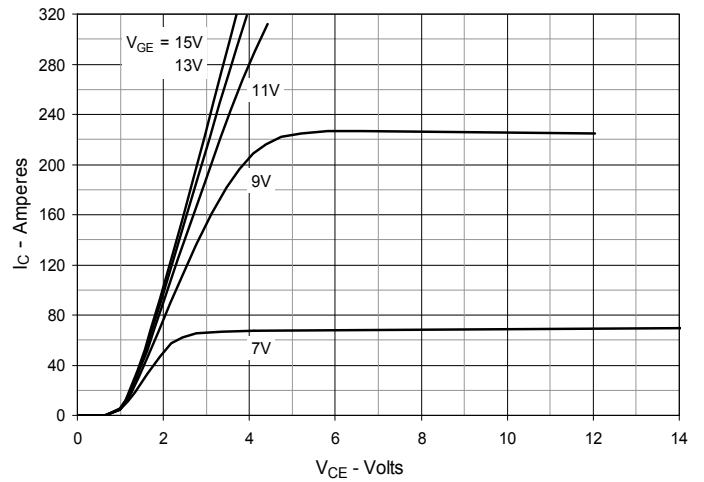


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

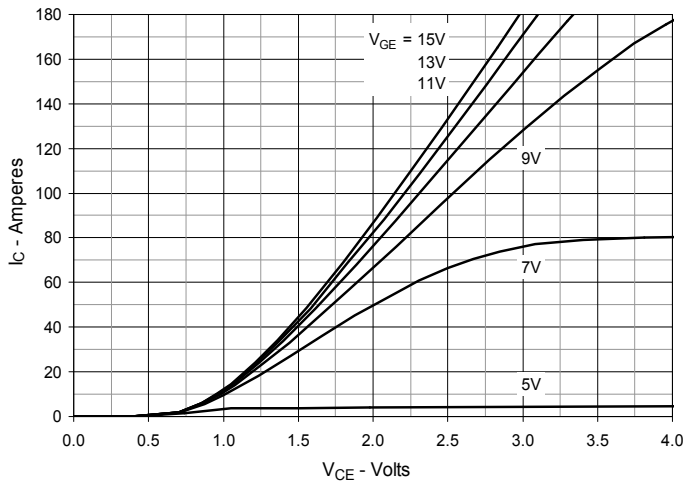


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

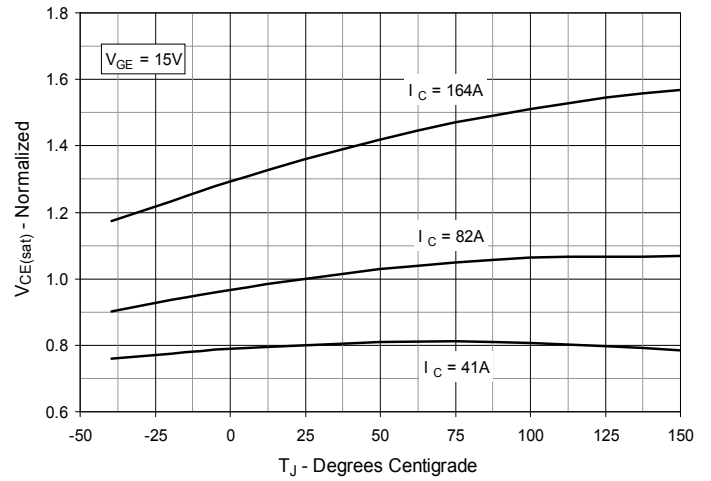


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

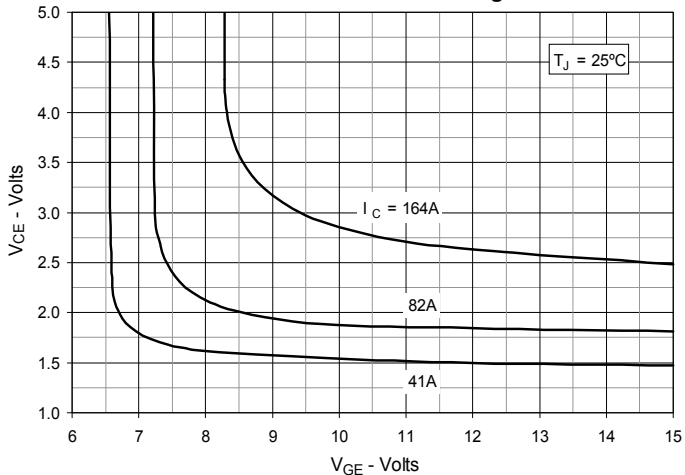


Fig. 6. Input Admittance

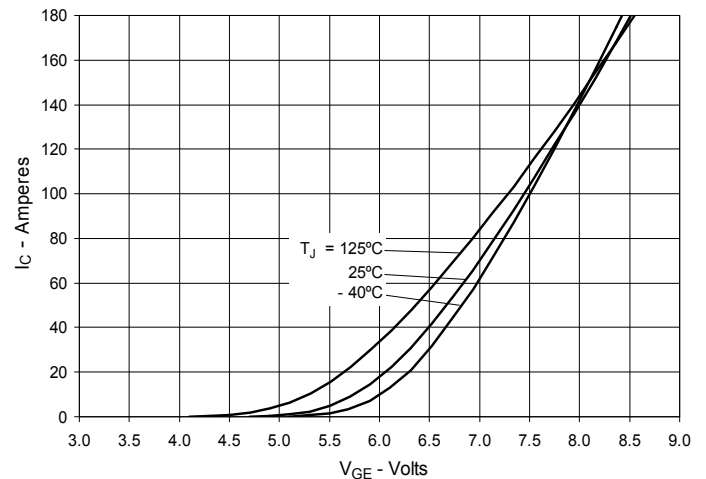


Fig. 7. Transconductance

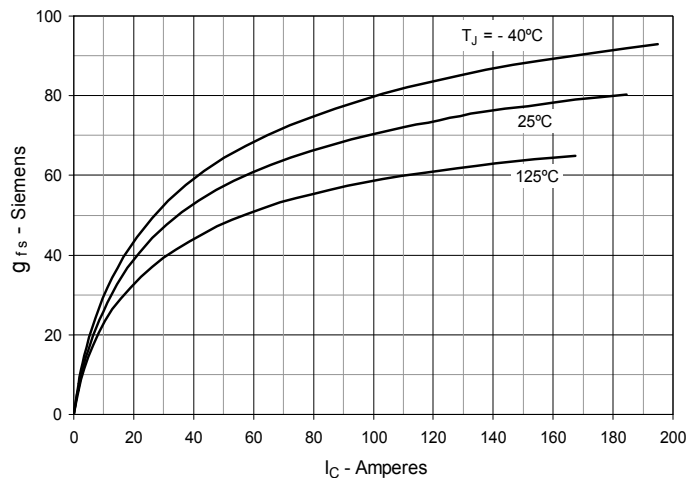


Fig. 8. Gate Charge

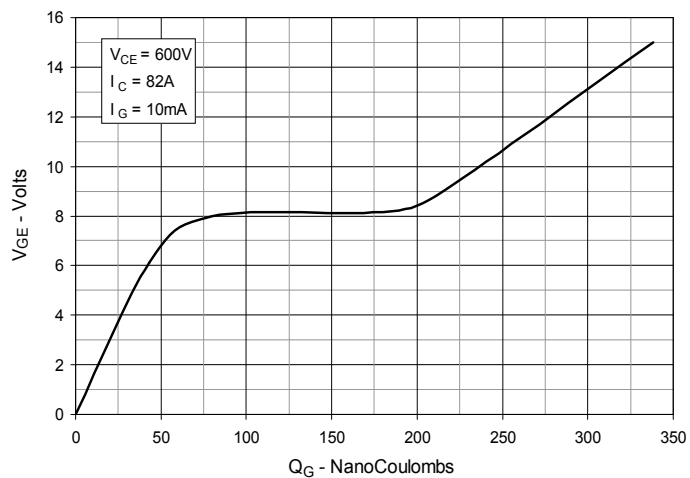


Fig. 9. Capacitance

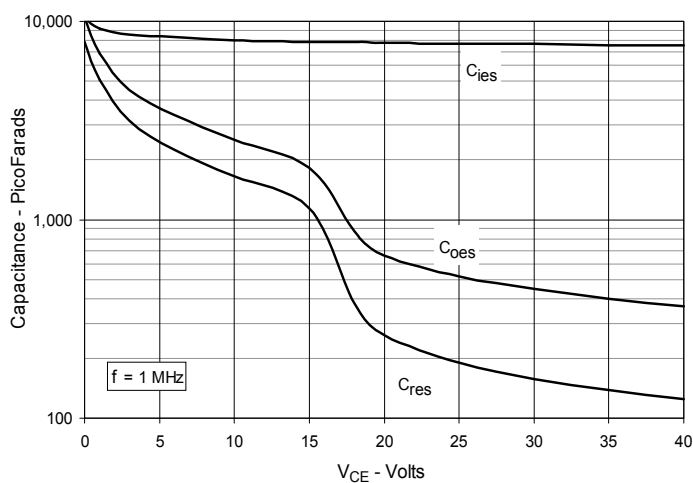


Fig. 10. Reverse-Bias Safe Operating Area

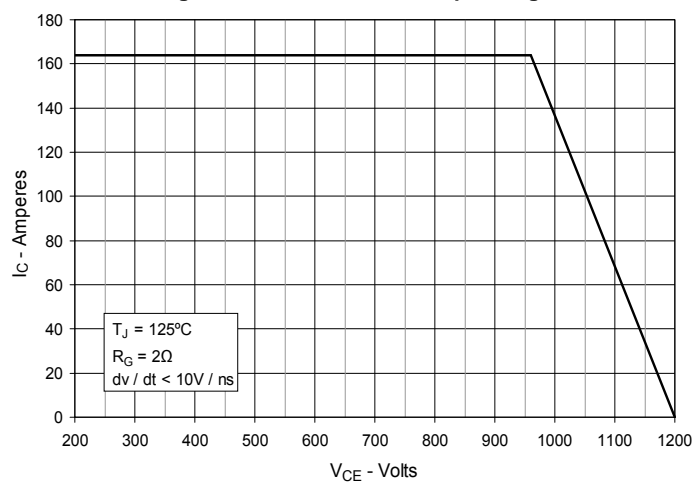


Fig. 11. Maximum Transient Thermal Impedance

